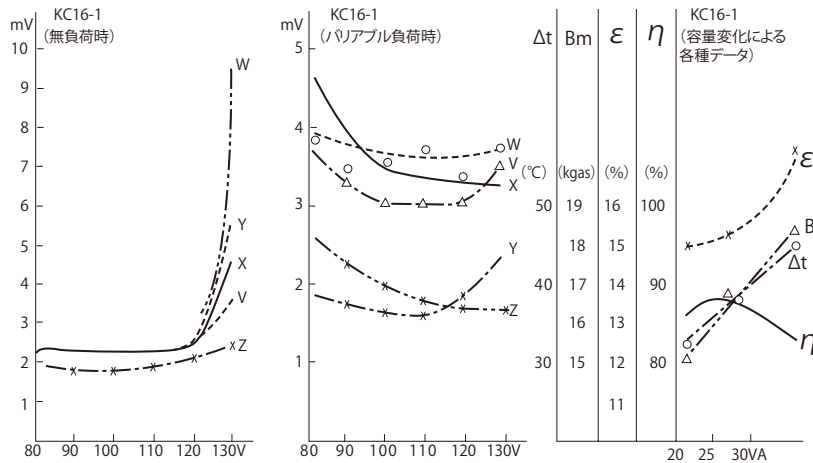
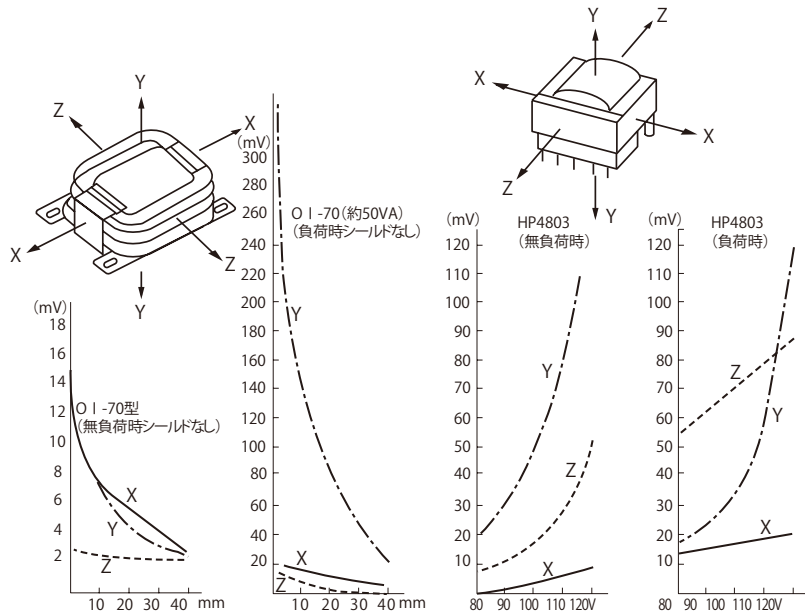
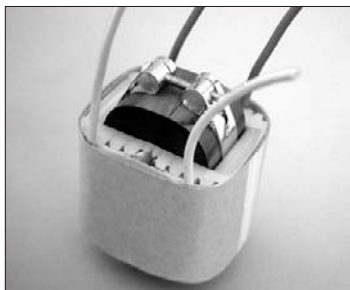
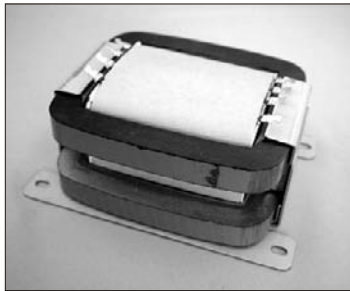




High Quality Transformers

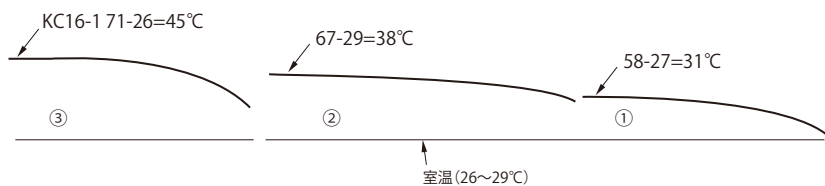
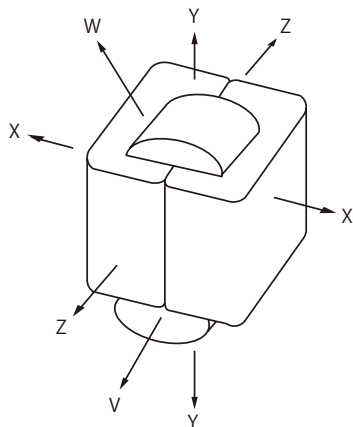
漏洩磁束等参考データ



KC16-1電源トランス(試作時実測参考データ)

	Vp	Ip	V2	I2	VA	η	V20	ε%	Bm
0.23φ1150T×2 (110V)	①100.5V	0.249A	30.6V	0.701A	21.4506VA	85.718%	35.2V	15.0	15.06
	②112V	0.28A	34.1V	0.795A	27.109VA	86.44%	39.3V	15.3	16.78
	③123V	0.31A	36.7V	0.872A	32.00VA	83.92%	43V	17.2	18.43
					(26.4VA)				
									0.4φ400T×2

静 (25°C)	①	②	③
(1-2)21.22Ω	23.70Ω(29.5°C)	24.41Ω(37.75°C)	24.86Ω(43%)
(3-4)2.826Ω	3.144Ω(28.25°C)	3.249Ω(37.5°C)	3.311Ω(43%)
	P/S	P/S	P/S
A/mm²	2.998A, 2.789A	3.371A, 3.163A	3.732A, 3.469A



理想 $M = \sqrt{L_1 L_2}$

実体 $M < \sqrt{L_1 L_2}$

$M = K \sqrt{L_1 L_2}$

$K = M / \sqrt{L_1 L_2}$

$K = \sqrt{1 - L_x / L_p}$

$K \leq 1$



High Quality Transformers

P12408 () 参考データ

P1 参考データ (試作時 実測参考データ at 50Hz)

